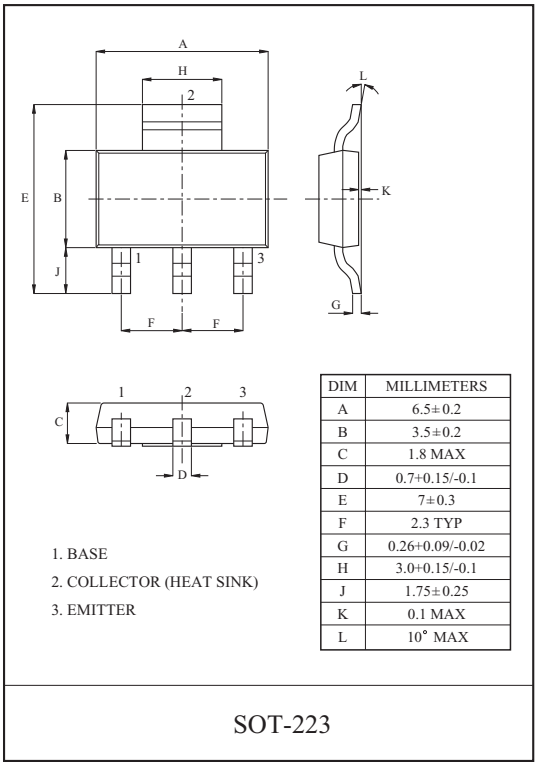
PZTA42

EPITAXIAL PLANAR NPN TRANSISTOR

HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

FEATURES

・Complementary to PZTA92.



DIM	MILLIMETERS
A	6.5±0.2
B	3.5±0.2
C	1.8 MAX
D	0.7+0.15/-0.1
E	7±0.3
F	2.3 TYP
G	0.26+0.09/-0.02
H	3.0+0.15/-0.1
J	1.75±0.25
K	0.1 MAX
L	10° MAX

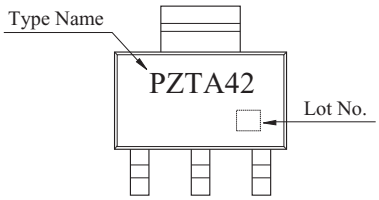
SOT-223

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	500	mA
Emitter Current	I_E	-500	mA
Collector Power Dissipation	P_C *	1	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55～150	℃

* Package Mounted On FR-4 PCB 36×18×1.5mm. :
mountina pad for the collector lead min.6cm²

Marking

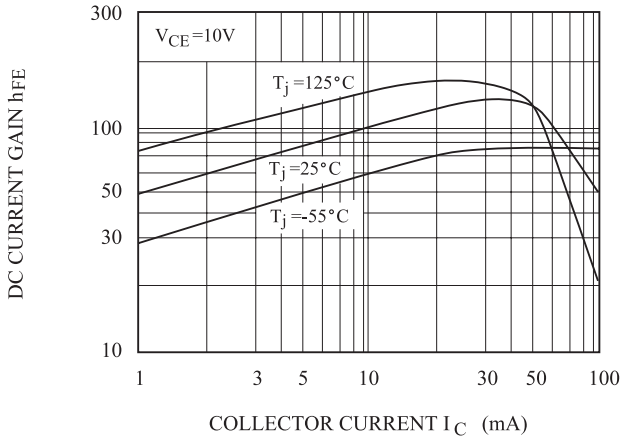


ELECTRICAL CHARACTERISTICS (Ta=25℃)

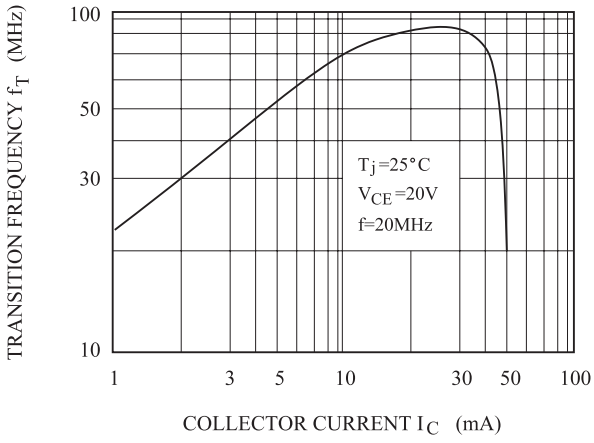
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100㎂, I_E=0	300	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BE)CEO}$	I_C=1.0mA, I_B=0	300	-	-	V
DC Current Gain	* h_{FE}	I_C=1.0mA, V_{CE}=10V	40	-	-	
		I_C=10mA, V_{CE}=10V	40	-	-	
		I_C=30mA, V_{CE}=10V	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=20mA, I_B=2.0mA	-	-	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=20mA, I_B=2.0mA	-	-	0.9	V
Transition Frequency	f_T	V_{CE}=20V, I_C=10mA, f=100MHz	50	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=20V, I_E=0, f=1MHz	-	-	3.0	pF

*Pulse Test : Pulse Width≦300㎲, Duty Cycle≦2.0%

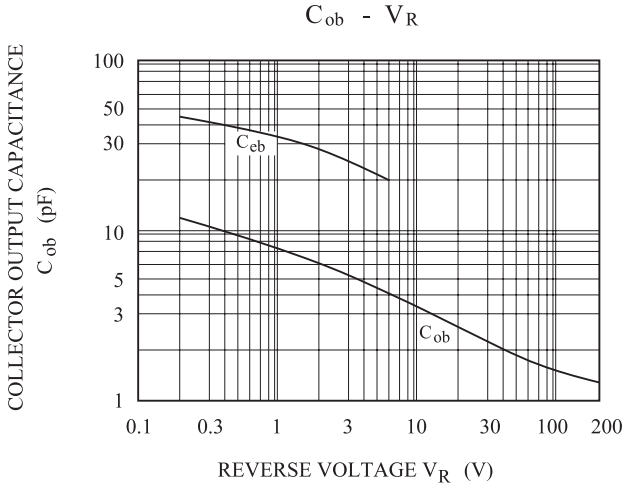
h_{FE} - I_C



f_T - I_C



C_{ob} - V_R



$V_{BE(sat)}$, $V_{CE(sat)}$ - I_C